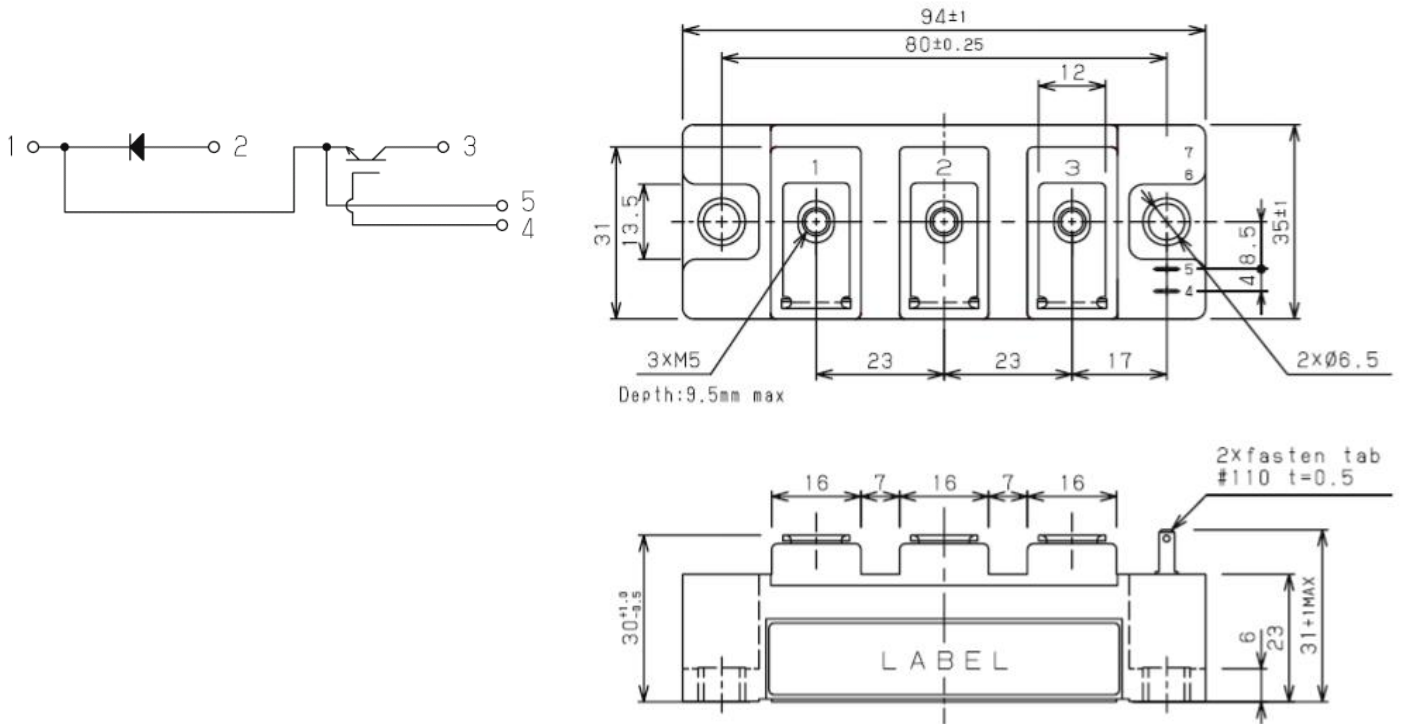


□ 回路図 : **CIRCUIT**

□ 概略図 : **SCHEMATIC DIAGRAM**

Dimension: [mm]


□ 最大定格 : **MAXIMUM RATINGS** (at T_c=25°C unless otherwise specified)

Item		Symbol	Condition	Rated Value	Unit
IGBT	コレクタ・エミッタ間電圧 Collector-Emitter Voltage	V _{CE} S	G-E Short	1200	V
	ゲート・エミッタ間電圧 Gate-Emitter Voltage	V _{GE} S	C-E Short	±20	V
	コレクタ電流 Collector Current	I _C	DC T _c =85°C	75	A
		I _{CP}	Pulse ≤ 1ms	150	
Diode	繰り返しピーク逆電圧 Repetitive peak reverse voltage	V _{RRM}	T _J =175°C	348	W
			T _J =150°C	290	
	順電流 Forward Current	I _F		75	A
		I _{FM}	Pulse ≤ 1ms	150	
最大接合温度 Maximum Junction Temperature		T _{JMAX}	瞬時動作(過負荷) Instantaneous Overload	175	°C
接合温度範囲 Junction Temperature Range		T _J		-40~+150	°C
保存温度範囲 Storage Temperature Range		T _{stg}		-40~+125	°C
絶縁耐圧 Isolation Voltage		V _{ISO}	Terminal to Base AC, 1minute	2,500	V (RMS)
締め付けトルク Mounting Torque	Module Base to Heatsink	F _{tor}	M6	3	N・m
	Busbar to Main Terminal		M5	2	

□ 電 気 的 特 性 : **ELECTRICAL CHARACTERISTICS** (at T_J=25°C unless otherwise specified)

Characteristic			Symbol	Test Condition	Min.	Typ.	Max.	Unit		
IGBT	コレクタ遮断電流 Collector-Emitter Cut-Off Current		ICES	VCE= 1200V,VGE= 0V		—	—	1.0	mA	
	ゲート漏れ電流 Gate-Emitter Leakage Current		IGES	VGE= ±20V,VCE= 0V		—	—	1.0	μA	
	コレクタ・エミッタ間飽和電圧 Collector-Emitter Saturation Voltage		VCE(sat.)	IC= 75A,VGE= 15V (chip level)	TJ=25°C	—	1.50	2.00	V	
					TJ=125°C	—	1.70	—		
					TJ=150°C	—	1.80	—		
	ゲートしきい値電圧 Gate-Emitter Threshold Voltage		VGE(th.)	VCE= 10V,IC= 2.5mA		4.8	—	7.0	V	
	入力容量 Input Capacitance		Cies	VCE= 25V,VGE= 0V,f= 1MHz		—	8.0	—	nF	
	出力容量 Output Capacitance		Coes			—	0.23	—		
	帰還容量 Reverse Transfer Capacitance		Cres			—	0.20	—		
	ゲート電荷量 Gate Charge		Qg	VCC=600V, IC=75A, VGE=-15~+15V		—	830	—	nC	
スイッチング時間 Switching Time	上昇時間 Rise Time	tr	VCC= 600V LS=38nH IC= 75A Inductive Load RG= 10Ω VGE= ±15V TJ= 150°C		—	60	—	ns		
	ターンオン遅延時間 Turn-on Delay Time	td(on)			—	110	—			
	下降時間 Fall Time	tf			—	180	—			
	ターンオフ遅延時間 Turn-off Delay Time	td(off)			—	500	—			
Diode	順電圧 Peak Forward Voltage		VF	IF= 75A,VGE=0V (chip level)	TJ=25°C	—	2.00	2.60	V	
	逆回復時間 Reverse Recovery Time				trr	TJ=125°C	—	1.98		—
						TJ=150°C	—	1.95		—
内部配線抵抗 Internal Lead Resistance			RCC+EE'	主端子—チップ間 / 1素子 Main Terminal - Chip / Per 1 Arm		—	—	1	mΩ	
内部インダクタンス Stray Inductance			LSCE	メイン端子3—2間 Main Terminal 3 - Main Terminal 2		—	30	—	nH	

□ 熱 的 特 性 : **THERMAL CHARACTERISTICS**

Characteristic		Symbol	Test Condition	Min.	Typ.	Max.	Unit
熱抵抗 Thermal Resistance	IGBT	R _{th(j-c)}	Junction to Case Per 1 Arm (T _c 測定点:チップ直下)	—	—	0.43	°C/W
	Diode			—	—	0.80	
接触熱抵抗 Thermal Resistance	IGBT	R _{th(c-f)}	Case to heatsink Per 1 Arm Paste=1W/(m ² •°C)	—	0.10	—	
	Diode			—	0.17	—	

特性図 : CHARACTERISTICS CURVES

Fig.1- Output Characteristics (Typical)

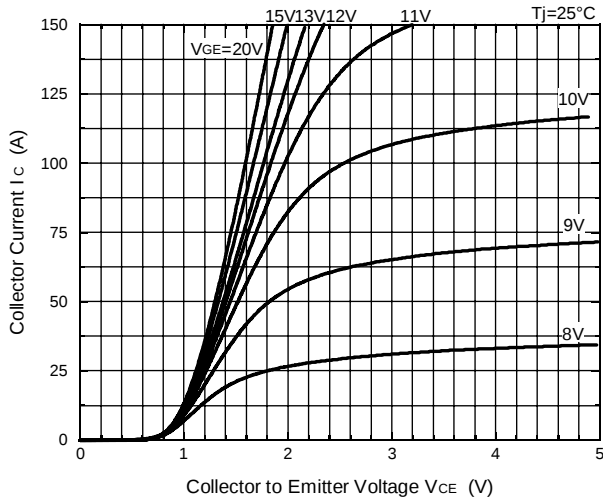


Fig.2- Saturation Voltage Characteristics (Typical)

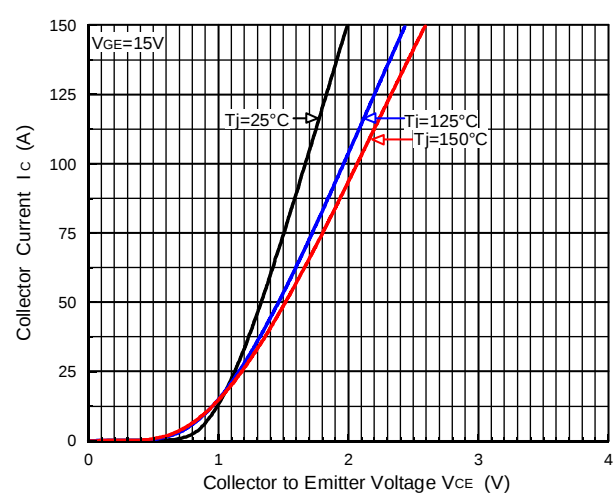


Fig.3- Transfer Characteristics (Typical)

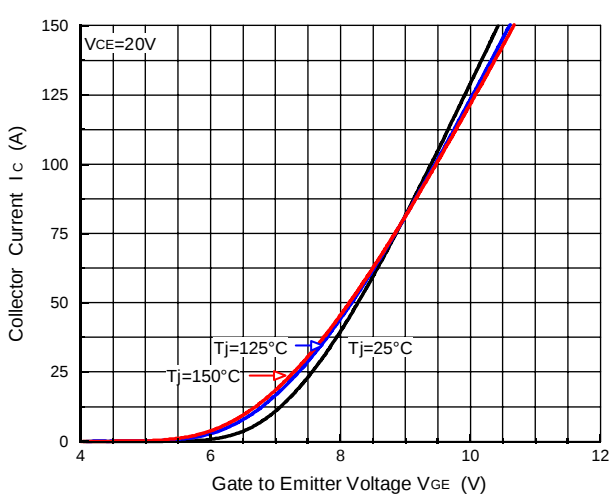


Fig.4- Gate Charge vs. Collector to Emitter Voltage (Typical)

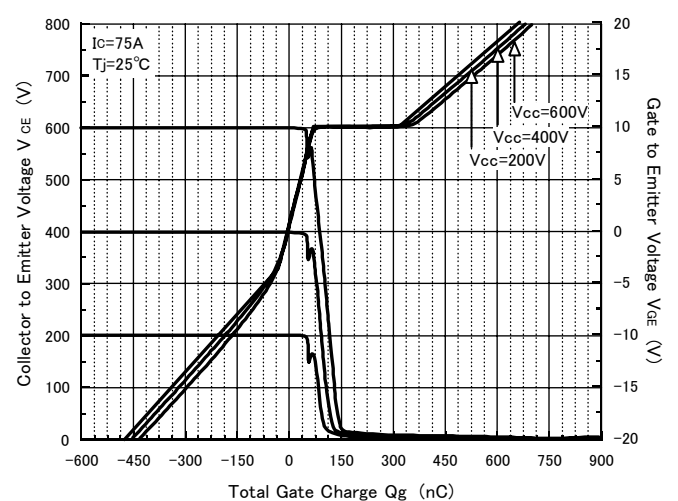


Fig.5- Collector Current vs. Switching Time

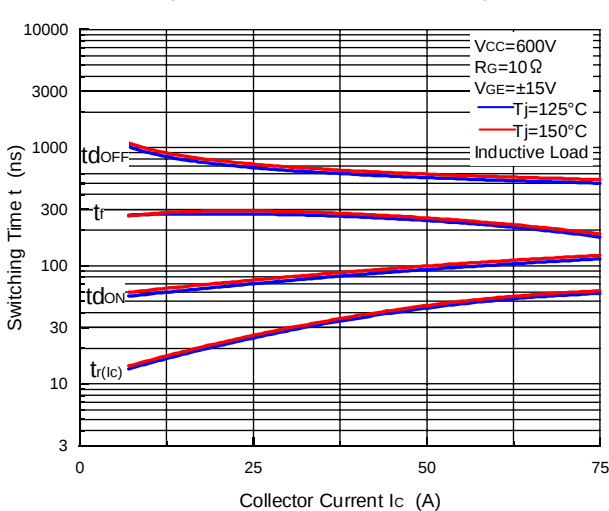
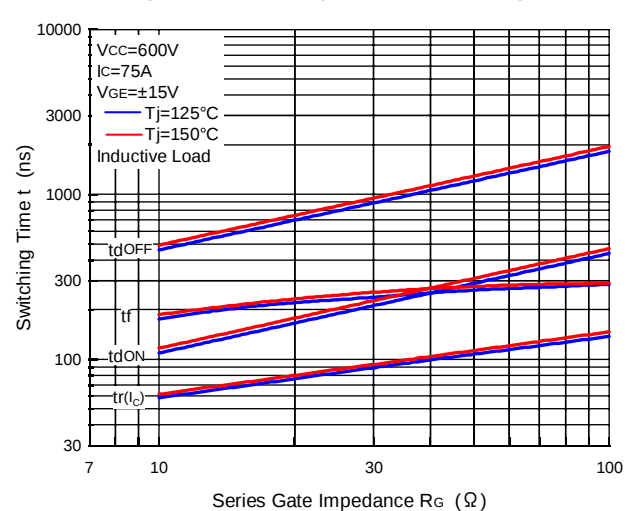


Fig.6- Series Gate Impedance vs. Switching Time



特性図 : CHARACTERISTICS CURVES

Fig.7- Collector Current vs. Switching Loss

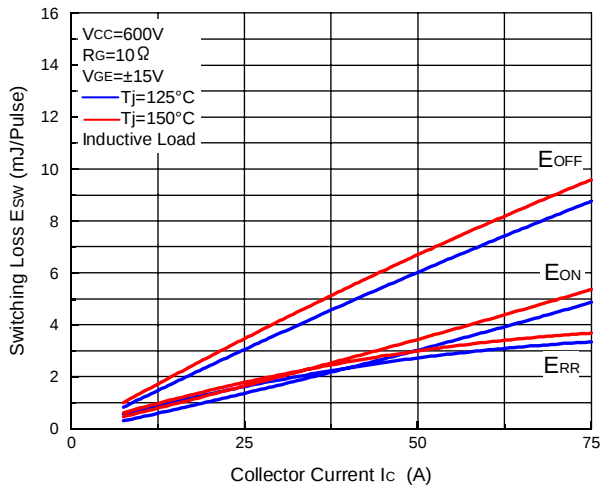


Fig.8- Series Gate Impedance vs. Switching Loss

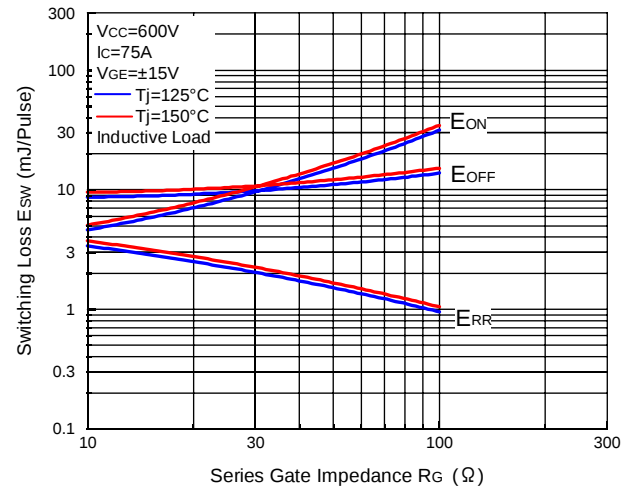


Fig.9- Forward Characteristics of FWD (Typical)

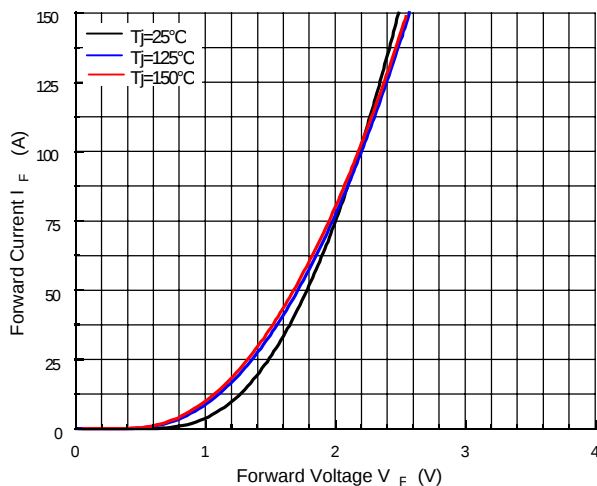


Fig.10- FWD Reverse Recovery Characteristics (Typical)

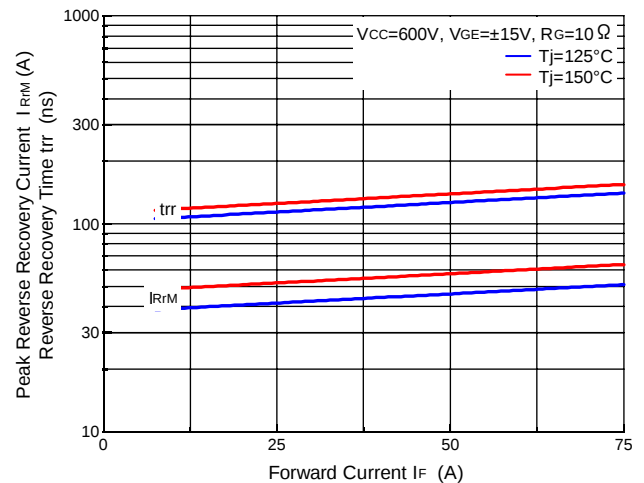


Fig.11- Reverse Bias Safe Operating Area

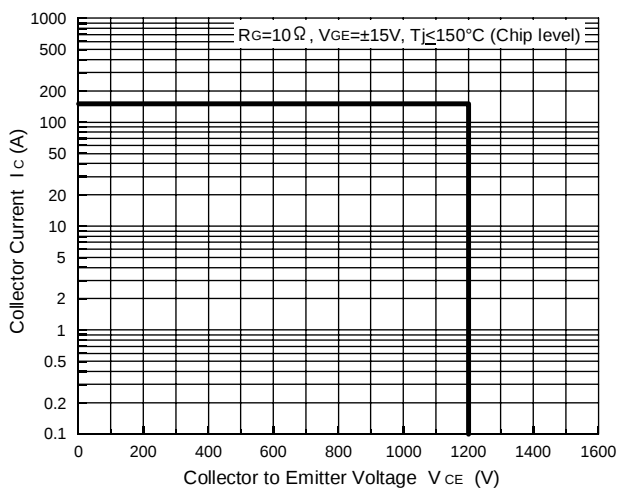


Fig.12- Transient Thermal Impedance

